TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC2878

For Muting and Switching Applications

High emitter-base voltage: VEBO = 25 V (min)

• High reverse hFE: Reverse hFE = 150 (typ.) ($V_{CE} = -2 \text{ V}$, $I_{C} = -4 \text{ mA}$)

• Low on resistance: $RON = 1 \Omega$ (typ.) (IB = 5 mA)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	25	V
Collector current	IC	300	mA
Base current	Ι _Β	60	mA
Collector power dissipation	P _C	400	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C

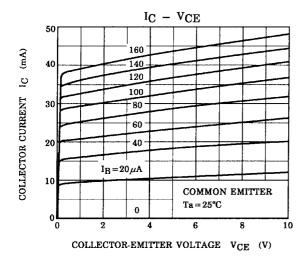
1. EMITTER 2. COLLECTOR 3. BASE JEDEC TO-92 JEITA SC-43 TOSHIBA 2-5F1B

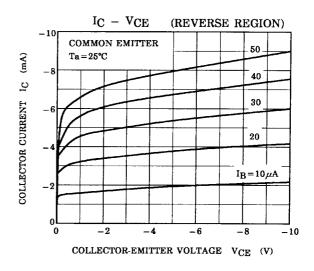
Weight: 0.21 g (typ.)

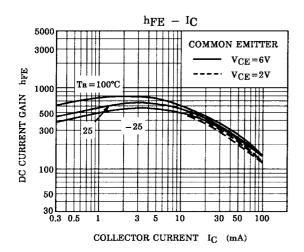
Electrical Characteristics (Ta = 25°C)

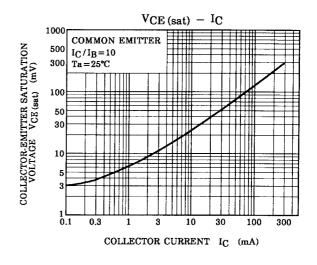
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I _{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$	_	_	0.1	μΑ
Emitter cut-off cu	rrent	I _{EBO}	V _{EB} = 25 V, I _C = 0	_	_	0.1	μΑ
DC current gain		h _{FE} (Note)	V _{CE} = 2 V, I _C = 4 mA	200	_	1200	
Collector-emitter	saturation voltage	V _{CE} (sat)	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$	_	0.042	0.1	V
Base-emitter volta	age	V _{BE}	V _{CE} = 2 V, I _C = 4 mA	_	0.61	_	V
Transition freque	ncy	f _T	V _{CE} = 6 V, I _C = 4 mA	_	30	_	MHz
Collector output capacitance		C _{ob}	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	4.8	7	pF
Switching time	Turn-on time	t _{on}	OUTPUT $10V \prod_{\mu \text{s}} V_{BB} V_{CC}$ $= -3V = 12V$ Duty cycle $\leq 2\%$		160	_	
	Storage time	t _{stg}		_	500	_	ns
	Fall time	t _f		_	130		

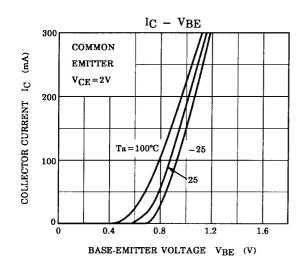
Note: hFE classification A: 200~700, B: 350~1200

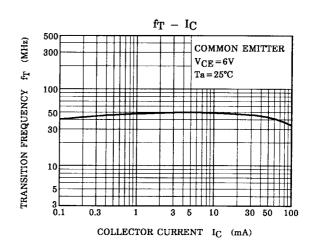




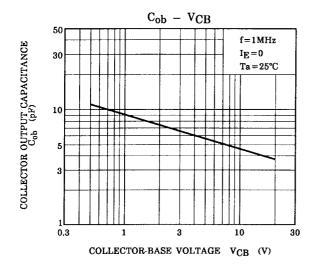


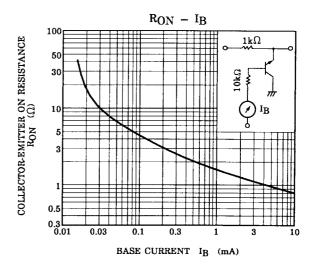


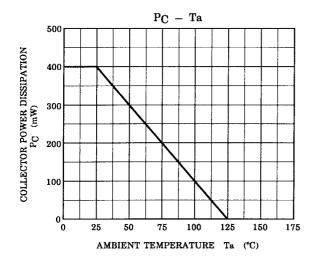




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